IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Fernando L Toledo
Serial No.:	10/602,323	Group Art Unit:	2823
Filed:	June 24, 2003	Docket:	1303.101US1
Title:	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,
KIE Y. AHN ET AL.

By their Representatives,
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Date 23 August 2004 By _____
David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 23rd day of August, 2004.

Amy Moriarty
Name

_____
Signature

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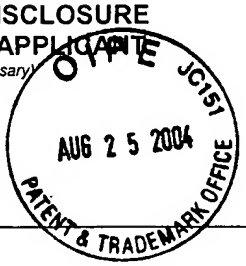

Sheet 1 of 5

Complete if Known

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First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Toledo, Fernando

Attorney Docket No: 1303.101US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-2003/0042526	03/06/2003	Weimer, Ronald A.	257	309	08/29/2001
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	US-6,683,005	01/27/2004	Sandhu, Gurtej S., et al.	438	715	01/17/2003

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	WO-0233729A2	04/25/2002	Fink, S. T.	H01J	37/32	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
		AARIK, JAAN , et al., "Influence of substrate temperature on atomic layer growth and properties of HfO/sub 2/ thin films", Thin Solid Films, 340(1-2), (1999),110-116	
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Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** *(Use as many sheets as necessary)*	*Complete if Known*	
	Application Number	10/602,323
	Filing Date	June 24, 2003
	First Named Inventor	Ahn, Kie
	Group Art Unit	2823
	Examiner Name	Toledo, Fernando
Sheet 2 of 5	Attorney Docket No: 1303.101US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	**Cite No [1]**	**Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.**	**T[2]**
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		Devices Meetings 2002, (2002),429-432	
		VAN DOVER, R. B., et al., "Amorphous lanthanide-doped TiOx dielectric films", Applied Physics Letters, 74(20), (May 17, 1999),3041-3043	
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COMMUNICATION CONCERNING RELATED APPLICATIONS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

Serial/Patent No.	Filing Date	Attorney Docket	Title
09/944,981	August 30, 2001	1303.021US1	GATE OXIDES AND METHODS OF FORMING
09/945,535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/028,643	December 20, 2001	1303.030US1	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/052,983 6,767,795	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027,315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
09/797,324	March 1, 2001	303.717US1	METHODS, SYSTEMS, AND APPARATUS FOR UNIFORM CHEMICAL-VAPOR DEPOSITIONS
10/099,194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELETRICS
10/081,439	February 20, 2002	1303.046US1	EVAPORATED LaAIO3 FILMS FOR GATE DIELECTRICS
10/137,058	May 2, 2002	303.802US1	ATOMIC LAYER DEPOSITION AND CONVERSION

10/137,168	May 2, 2002	1303.048US1	METHODS FOR ATOMIC-LAYER DEPOSITION OF ALUMINUM OXIDES IN INTEGRATED CIRCUITS
10/137,499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS
10/163,481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO3 FILMS FOR GATE DIELECTRICS
10/163,686	June 5, 2002	1303.059US1	Pr2O3-BASED La-oxide GATE DIELECTRICS
10/209,581	July 30, 2002	1303.061US1	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO2/ZrO2 FILMS AS GATE DIELECTRICS
10/219,870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS BY PLASMA OXIDATION
10/219,878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/229,903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233,309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiOx DIELECTRIC FILMS
10/309,583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI4
10/309,935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn-Ti-O FILMS
10/379,470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS

10/403,734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAlxOy DIELECTRIC LAYERS
10/420,307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO4 FILMS
10/602,315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
09/779,959 6,495,436	February 9, 2001		IFORMATION OF METAL OXIDE GATE DIELECTRIC
09/838,335 6,514,828	April 20, 2001		METHOD OF FABRICATING A HIGHLY RELIABLE GATE OXIDE
09/881,408	June 13, 2001		Dielectric layer forming method and devices formed therewith
09/908,767 6,534,420	July 18, 2001		METHODS FOR FORMING DIELECTRIC MATERIALS AND METHODS FOR FORMING SEMICONDUCTOR DEVICES
10/765,619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/7685,97	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789,042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELETRICS
10/789,044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiOx DIELECTRIC FILMS
	October 10, 2003		LANTHANIDE OXIDE/ ZIRCONIUM OXIDE ATOMIC LAYER DEPOSITED NANOLAMINATE GATE DIELECTRICS

10/052,983	January 17, 2002		HIGHLY RELIABLE AMORPHOUS HIGH K GATE DIELECTRIC ZROXNY
10/225,715	August 21, 2002		COMPOSITE DIELECTRIC FORMING METHODS AND COMPOSITE DIELECTRICS
10/352,507	January 27, 2003		ATOMIC LAYER DEPOSITION OF METAL OXYNITRIDE LAYERS AS GATE DIELECTRICS AND SEMICONDUCTOR DEVICE STRUCTURES UTILIZING METAL OXYNITRIDE LAYERS
10/863,953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
09/779,959 6,495,436	February 9, 2001		IFORMATION OF METAL OXIDE GATE DIELECTRIC
09/838,335 6,514,828	April 20, 2001		METHOD OF FABRICATING A HIGHLY RELIABLE GATE OXIDE
09/881,408	June 13, 2001		Dielectric layer forming method and devices formed therewith
09/908,767 6,534,420	July 18, 2001		METHODS FOR FORMING DIELECTRIC MATERIALS AND METHODS FOR FORMING SEMICONDUCTOR DEVICES

Respectfully submitted,
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Date 23 August 2004 By _____
David R. Cochran
Reg. No. 46,632

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 23rd day of August, 2004.

Name Amy Moriarty

Signature _____